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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via salesaddresses@nexperia.com). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET

For a complete data sheet, please also download:

- The IC04 LOCMOS HE4000B Logic Family Specifications HEF, HEC
- The IC04 LOCMOS HE4000B Logic Package Outlines/Information HEF, HEC

HEF4007UB

gates

Dual complementary pair and inverter

Product specification
File under Integrated Circuits, IC04

January 1995

Dual complementary pair and inverter

HEF4007UB gates

DESCRIPTION

The HEF4007UB is a dual complementary pair and an inverter with access to each device. It has three n-channel and three p-channel enhancement mode MOS transistors.

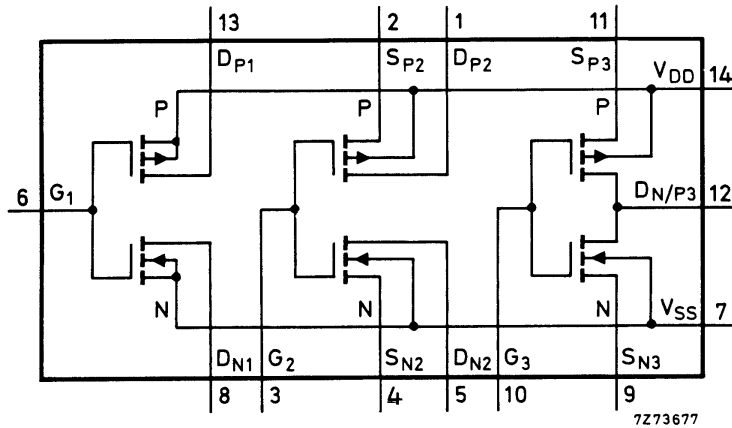


Fig.1 Schematic diagram.

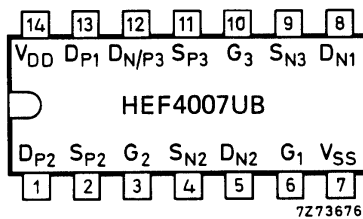


Fig.2 Pinning diagram.

PINNING

- SP₂, SP₃ source connections to 2nd and 3rd p-channel transistors
- DP₁, DP₂ drain connections from the 1st and 2nd p-channel transistors
- DN₁, DN₂ drain connections from the 1st and 2nd n-channel transistors
- SN₂, SN₃ source connections to the 2nd and 3rd n-channel transistors
- DN/P₃ common connection to the 3rd p-channel and n-channel transistor drains
- G₁ to G₃ gate connections to n-channel and p-channel of the three transistor pairs

- HEF4007UBP(N): 14-lead DIL; plastic (SOT27-1)
- HEF4007UBD(F): 14-lead DIL; ceramic (cerdip) (SOT73)
- HEF4007UBT(D): 14-lead SO; plastic (SOT108-1)
- (): Package Designator North America

FAMILY DATA, I_{DD} LIMITS category GATES

See Family Specifications for V_{IH}/V_{IL} unbuffered stages

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	V_{DD} V	SYMBOL	TYP.	MAX.		TYPICAL EXTRAPOLATION FORMULA
Propagation delays $G_n \rightarrow D_N$; D_P HIGH to LOW	5	t_{PHL}	40	80	ns	$13 \text{ ns} + (0,55 \text{ ns/pF}) C_L$
	10		20	40	ns	$9 \text{ ns} + (0,23 \text{ ns/pF}) C_L$
	15		15	30	ns	$7 \text{ ns} + (0,16 \text{ ns/pF}) C_L$
LOW to HIGH	5	t_{PLH}	40	75	ns	$13 \text{ ns} + (0,55 \text{ ns/pF}) C_L$
	10		20	40	ns	$9 \text{ ns} + (0,23 \text{ ns/pF}) C_L$
	15		15	30	ns	$7 \text{ ns} + (0,16 \text{ ns/pF}) C_L$
Output transition times HIGH to LOW	5	t_{THL}	60	120	ns	$10 \text{ ns} + (1,0 \text{ ns/pF}) C_L$
	10		30	60	ns	$9 \text{ ns} + (0,42 \text{ ns/pF}) C_L$
	15		20	40	ns	$6 \text{ ns} + (0,28 \text{ ns/pF}) C_L$
LOW to HIGH	5	t_{TLH}	60	120	ns	$10 \text{ ns} + (1,0 \text{ ns/pF}) C_L$
	10		30	60	ns	$9 \text{ ns} + (0,42 \text{ ns/pF}) C_L$
	15		20	40	ns	$6 \text{ ns} + (0,28 \text{ ns/pF}) C_L$

	V_{DD} V	TYPICAL FORMULA FOR P (μ W)	
Dynamic power dissipation per package (P)	5	$4500 f_i + \sum (f_o C_L) \times V_{DD}^2$	where f_i = input freq. (MHz) f_o = output freq. (MHz) C_L = load capacitance (pF) $\sum(f_o C_L)$ = sum of outputs V_{DD} = supply voltage (V)
	10	$20\,000 f_i + \sum (f_o C_L) \times V_{DD}^2$	
	15	$50\,000 f_i + \sum (f_o C_L) \times V_{DD}^2$	

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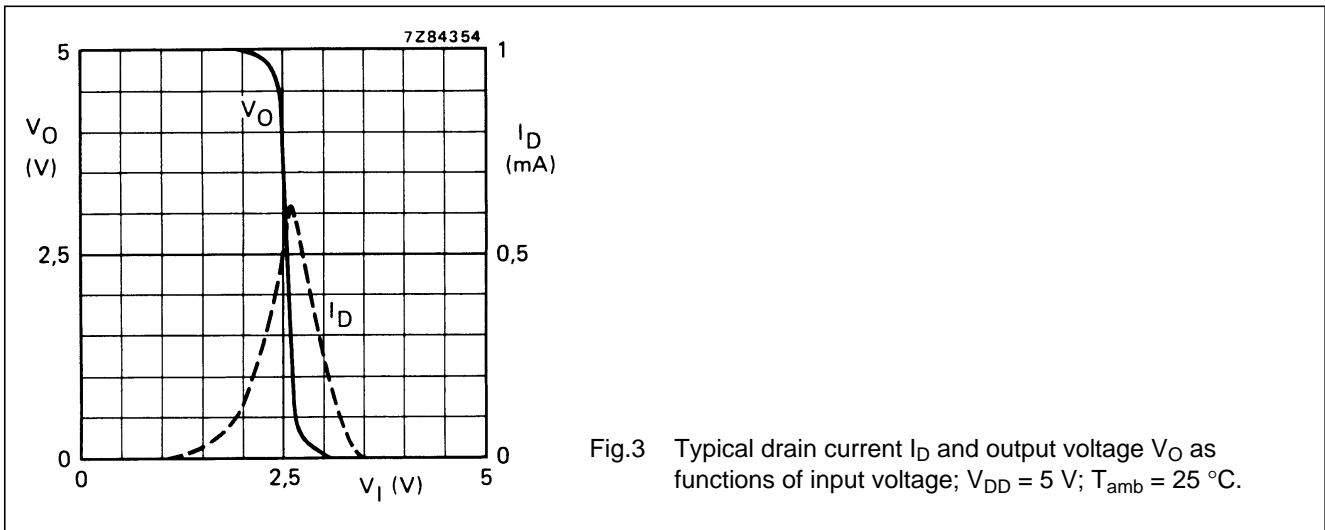


Fig.3 Typical drain current I_D and output voltage V_O as functions of input voltage; $V_{DD} = 5$ V; $T_{amb} = 25$ °C.

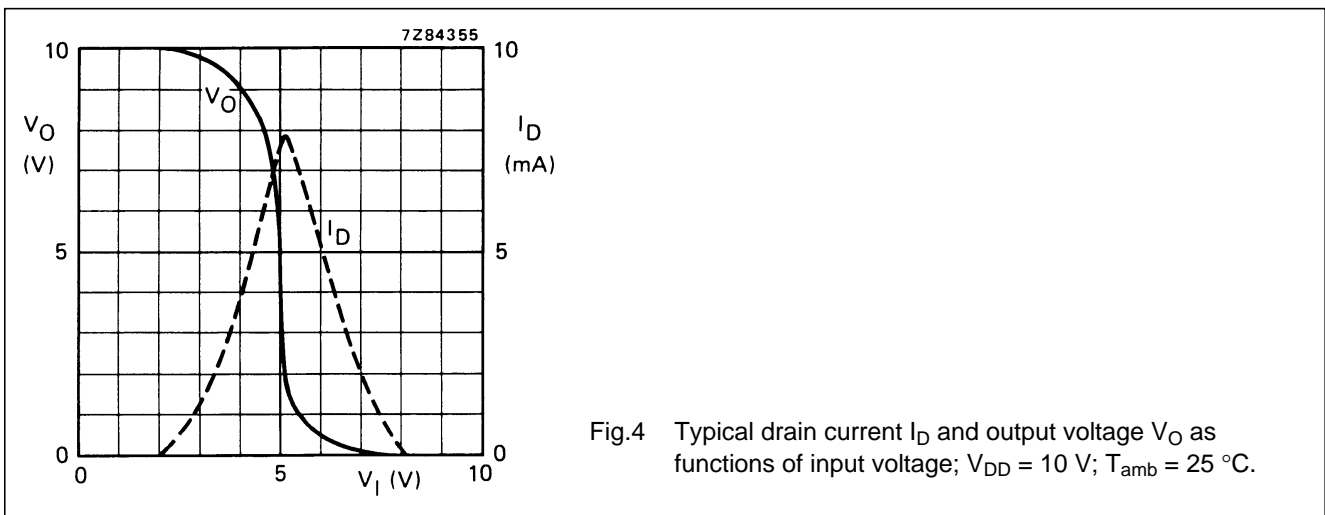


Fig.4 Typical drain current I_D and output voltage V_O as functions of input voltage; $V_{DD} = 10$ V; $T_{amb} = 25$ °C.

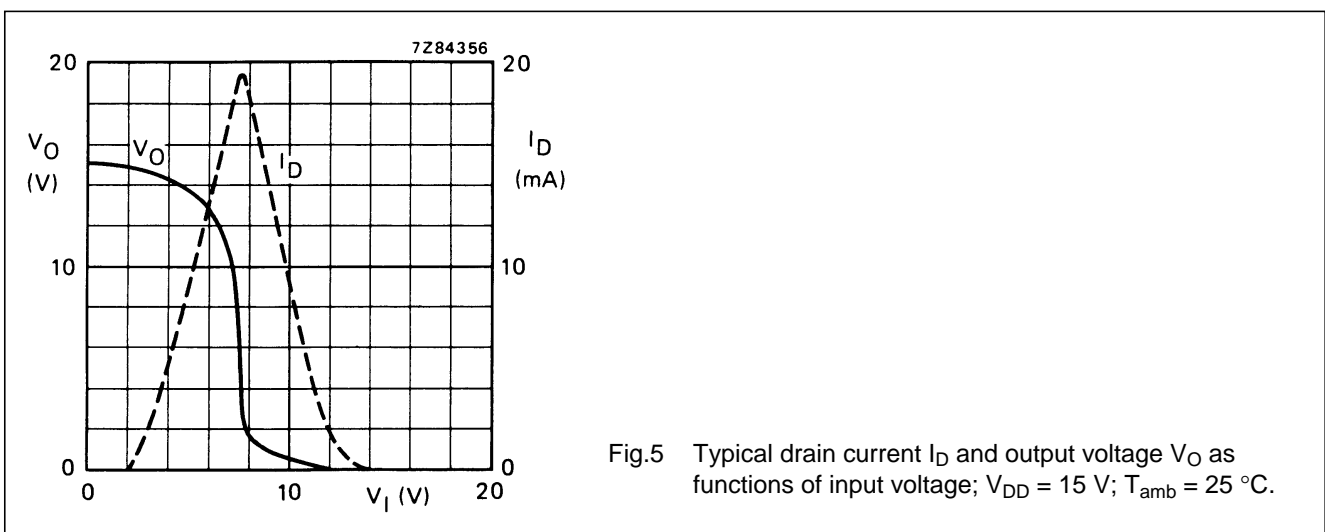


Fig.5 Typical drain current I_D and output voltage V_O as functions of input voltage; $V_{DD} = 15$ V; $T_{amb} = 25$ °C.

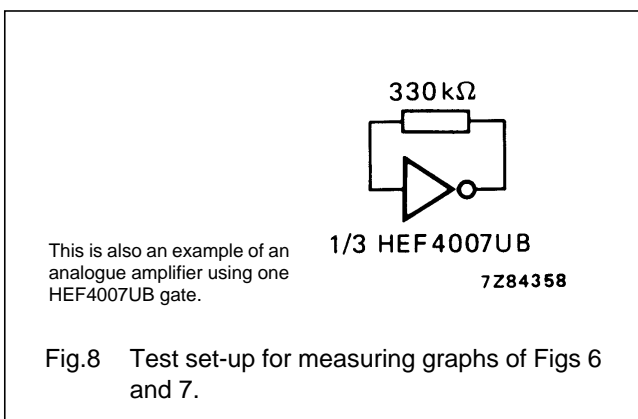
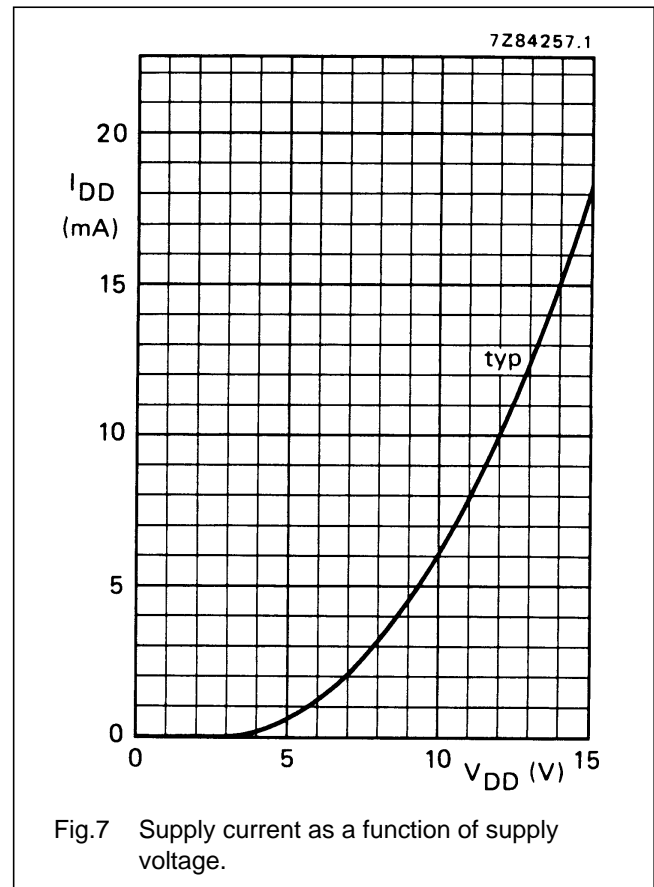
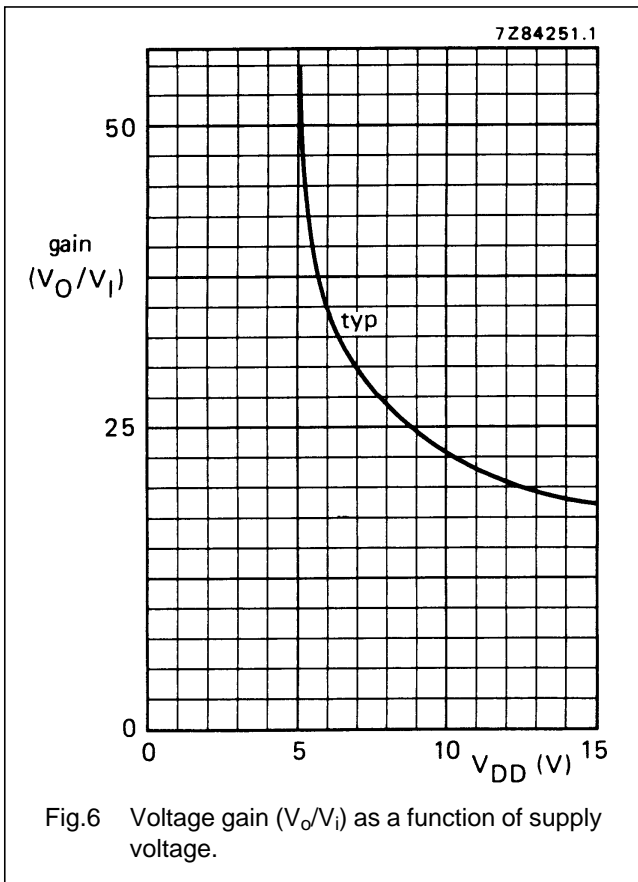
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APPLICATION INFORMATION

Some examples of applications for the HEF4007UB are:

- High input impedance amplifiers
- Linear amplifiers
- (Crystal) oscillators
- High-current sink and source drivers
- High impedance buffers.



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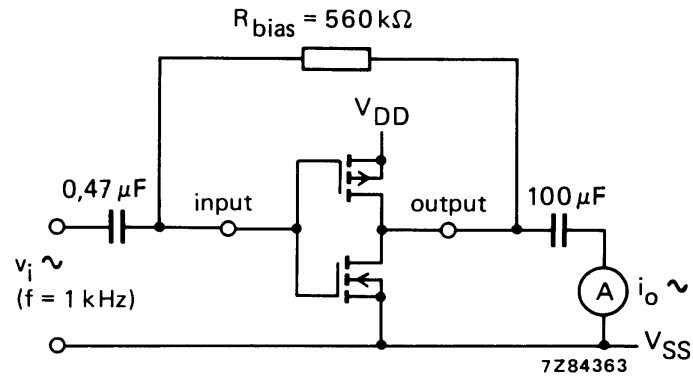
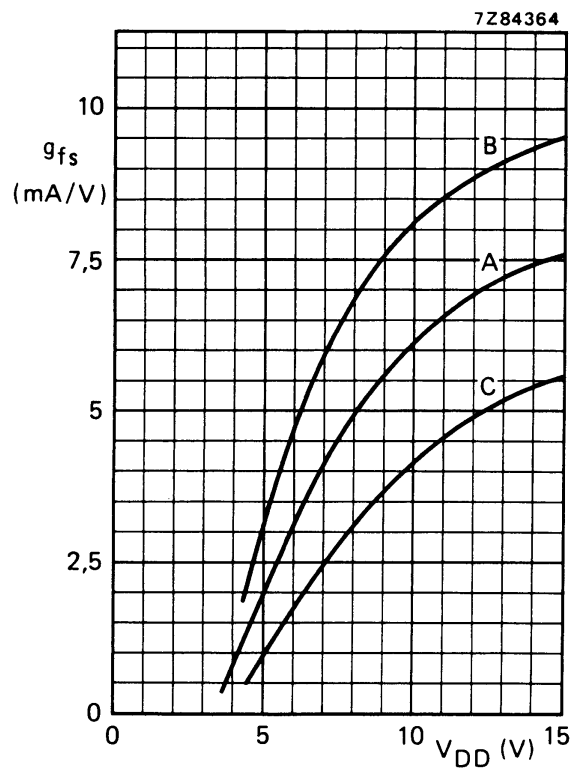


Fig.9 Test set-up for measuring forward transconductance $g_{fs} = di_o/dv_i$ at v_o is constant (see also graph Fig.10).



A: average,
 B: average + 2 s,
 C: average - 2 s, in where 's' is the observed standard deviation.

Fig.10 Typical forward transconductance g_{fs} as a function of the supply voltage at $T_{amb} = 25\text{ }^\circ\text{C}$.

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Figures 11 to 14 show some applications in which the HEF4007UB is used.

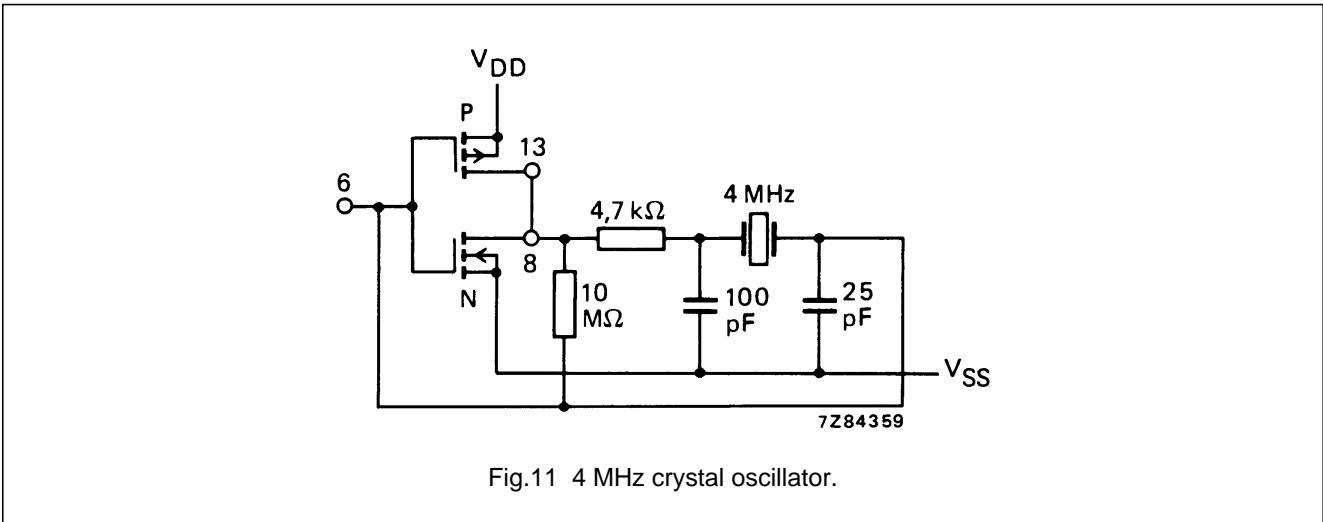


Fig.11 4 MHz crystal oscillator.

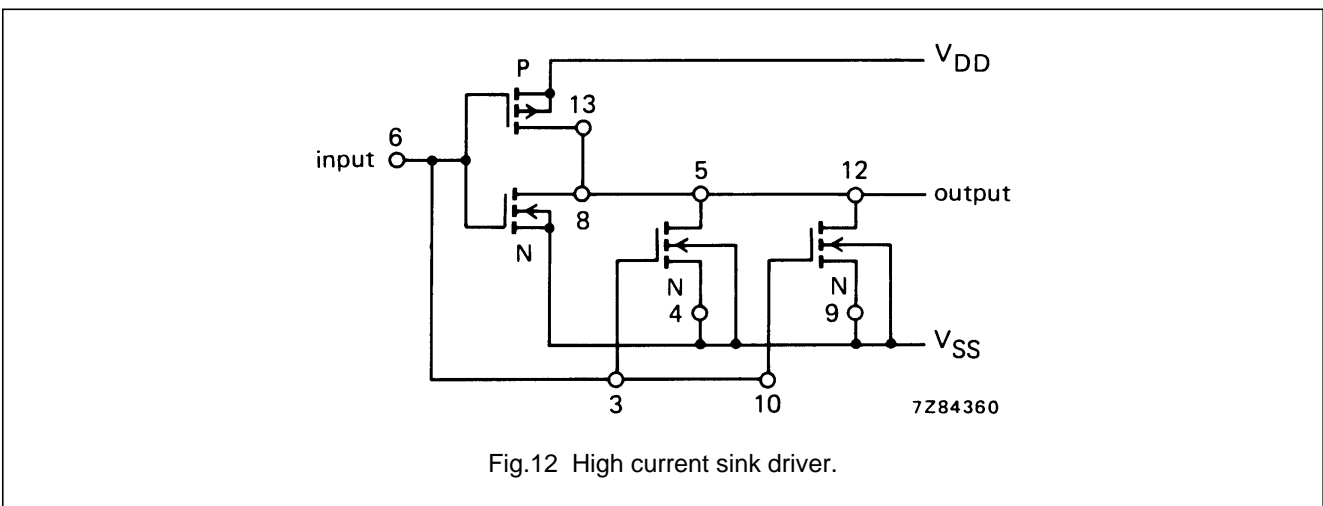


Fig.12 High current sink driver.

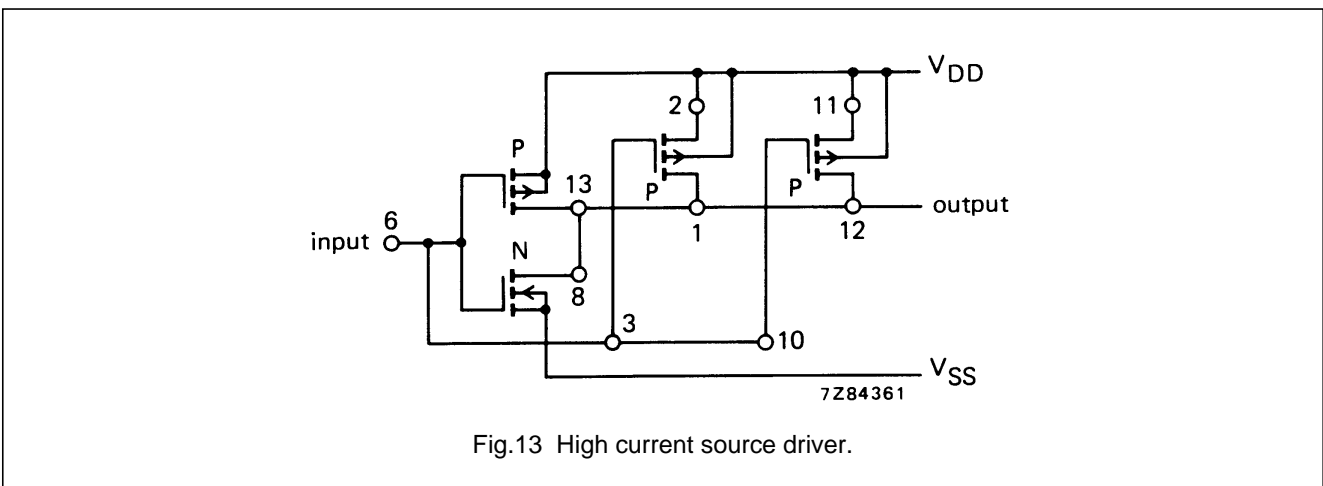


Fig.13 High current source driver.

